AMENDMENTS TO CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1-12. (Canceled)

13. (Previously Presented) A chemical mechanical polishing mixture, the mixture comprising:

(a) a solution comprising:

an etchant selected from the group consisting of: a peroxide, a nitrate, a halogen-containing compound, a sulphate, a persulphate, an oxidizer, an inorganic acid or a salt thereof, and mixtures thereof, wherein the inorganic acid is selected from the group consisting of nitric acid, iodic acid, periodic acid, perbromic acid, perchloric acid and perboric acid;

a modifier; and

a surfactant; and

(b) a plurality of particles having an average particle diameter ranging from 500 to 2000 μm.

14. (Currently Amended) The chemical mechanical polishing mixture of claim 13 wherein said mixture has a ~~volid~~ void volume ratio is about one or less.

15. (Previously Presented) The chemical mechanical polishing mixture of claim 13 wherein the solution further comprises a solvent.

16. (Canceled)

17. (Canceled)

18. (Previously Presented) The chemical mechanical polishing mixture of claim 13 wherein the modifier is at least one member selected from the group consisting of organic acids; amines; nitrogen-containing cyclic compounds; and combinations thereof.

19. (Previously Presented) The chemical mechanical polishing mixture of claim 15 wherein said solution comprises said etchant present in an amount from about 0.1 wt. % to about 20 wt. %; said modifier present in an amount of about 0.1 wt. % to about 15 wt%; said surfactant present in an amount from about 0.001 wt. % to about 10 weight percent; and said solvent present in an amount of about 50 wt. % to about 99 wt. %.

20. (Canceled)

21. (Previously Presented) The chemical mechanical polishing mixture of claim 19 wherein the particles comprise non-abrasive particles.

22. (Previously Presented) The chemical mechanical polishing mixture of claim 19 wherein the particles are comprised of at least one member selected from the group consisting of aluminum oxide, silicon dioxide, silicon carbide, titanium oxide, magnesium oxide, zirconium oxide, porcelain, cerium oxide, and combinations thereof.

23. (Previously Presented) The chemical mechanical polishing mixture of claim 13 wherein the particles have an average particle diameter ranging from 1000 to 2000 μm.

24. (Previously Presented) The chemical mechanical polishing mixture of claim 19 wherein the particles have an average particle diameter ranging from 1000 to 2000 μm.

25. (Previously Presented) The chemical mechanical polishing mixture of claim 14 wherein the modifier is at least one member selected from the group consisting of organic acids; amines; nitrogen-containing cyclic compounds; and combinations thereof.

27. (Previously Presented) The chemical mechanical polishing mixture of claim 14 wherein the solution further comprises a solvent.

28. (Previously Presented) The chemical mechanical polishing mixture of claim 27 wherein said solution comprises said etchant present in an amount from about 0.1 wt. % to about 20 wt. %, said modifier present in an amount of about 0.1 wt. % to about 15 wt%; said surfactant present in an amount from about 0.001 wt. % to about 10 weight percent; and said solvent present in an amount of about 50 wt. % to about 99 wt. %.

29. (Previously Presented) The chemical mechanical polishing mixture of claim 28 wherein the particles comprise non-abrasive particles.

30. (Previously Presented) The chemical mechanical polishing mixture of claim 28 wherein the particles are comprised of at least one member selected from the group consisting of aluminum oxide, silicon dioxide, silicon carbide, titanium oxide, magnesium oxide, zirconium oxide, porcelain, cerium oxide, and combinations thereof.

31. (Previously Presented) The chemical mechanical polishing mixture of claim 14 wherein the particles have an average particle diameter ranging from 1000 to 2000 μm.

32. (Previously Presented) The chemical mechanical polishing mixture of claim 28 wherein the particles have an average particle diameter ranging from 1000 to 2000 μm.